

Form PTO-1449 U.S. DEPARTMENT OF COMMERCE (REV. 7-80) PATENT AND TRADEMARK OFFICE				Atty. Docket No. GB 010121		Serial No.		
				Applicant Mark A. GAJDA				
				Filing Date CONCURRENTLY		Group 2823		
INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)								
U.S. PATENT DOCUMENTS								
Ex. Int.		Document Number	Date	Name	Class	Sub-class	Filing Date If Approp.	
WLL	AA	6 0 8 7 2 2 4	7/11/2000	Luo	438	270		
	AB							
	AC							
	AD							
	AE							
	AF							
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Sub-class	Trans.	
							Yes	No
WLL	AG	W 0 0 2 1 5 2 5 4	2/21/2002	PCT	H01L	21/336		
	AH							
	AI							
	AJ							
	AK							
OTHER (Including Author, Title, Date, Pertinent Pages, Etc.)								
WLL	AL	VISPSD' 2000 Proceedings, pages 181-184						
	AM							
	AN							
Examiner <u>WLL</u> Date Considered <u>9/5/03</u>								
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.								

MAY 30 2003

PATENT & TRADEMARK OFFICE

Sheet 1 of 1

Form PTO-1449 COMMERCE (REV. 7-80)		U.S. DEPARTMENT OF PATENT AND TRADEMARK OFFICE		Atty. Docket No. GB 010121		Serial No. 10/197,651	
INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				Applicant MARK A. GAJDA			
				Filing 7/17/02		Group 2842 2823	
U.S. PATENT DOCUMENTS							
Ex. Int.		Document Number	Date	Name	Class	Sub-class	Filing Date If Approp.
	AA						
	AB						
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	AE						
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FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub-class	Trans. Yes No
WLL	AC	1 9 5 0 7 1 4 6 A	11/1/96	GERMANY	H01L	29/78	X
WLL	AH	W 0 0 1 6 5 6 0 8	7/9/01	PCT (WORLD)	H01L	29/78	X
	AI						
	AJ						
	AK						
OTHER (Including Author, Title, Date, Pertinent Pages, Etc.)							
WLL	AL	Juang et al: "A process simplification scheme for fabricating self-aligned silicided trench-gate power MOSFETs" solid state Electronics, Elsevier Science Publishers, vol. 45, no. 1, January 2001, pages 169-172					
WLL	AM	Norstrom et al: "Formation of CoSi2 and TiSi2 on narrow poly-Si lines" Microelectronic engineering, vol. 14, no. 3-4, September 1991, pages 327-339					
	AN						
Examiner <i>WLL</i>				Date Considered 9/03/03			
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